

FIG. 1

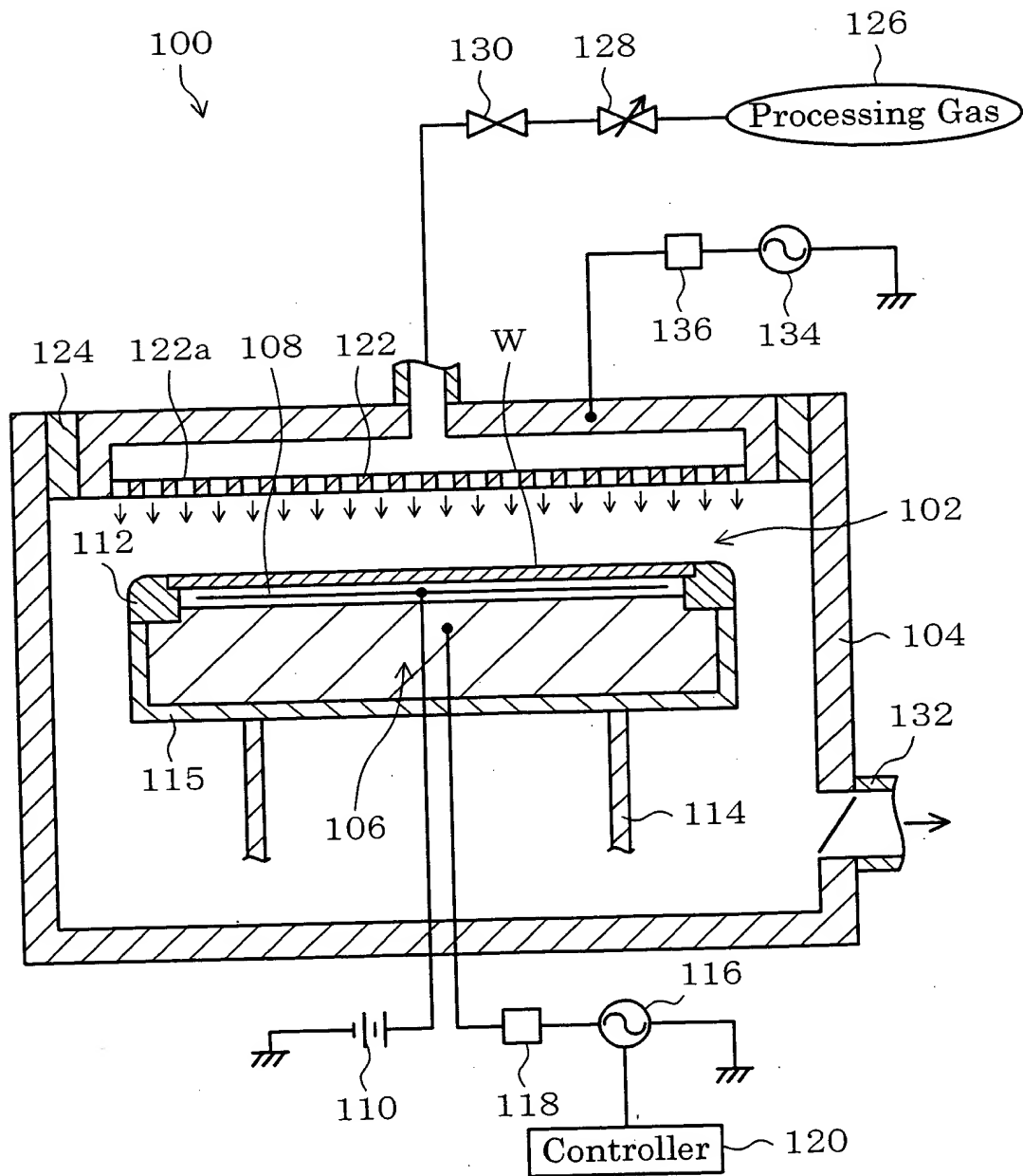


FIG.2(a)

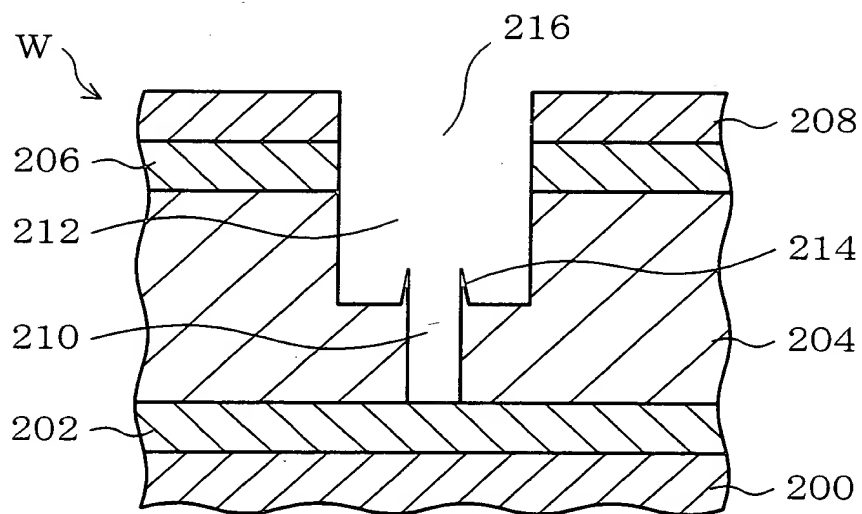


FIG.2(b)

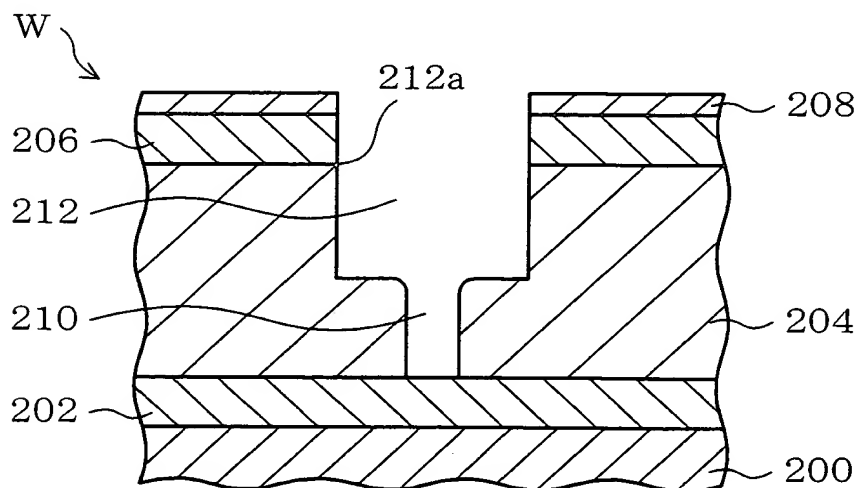


Figure 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 200, a base layer 202, a first layer 210, and a second layer 212. A trench 210a is formed in the first layer 210, and a second layer 212a is formed in the trench 210a. A width W is indicated for the trench 210a.

FIG.3(a)

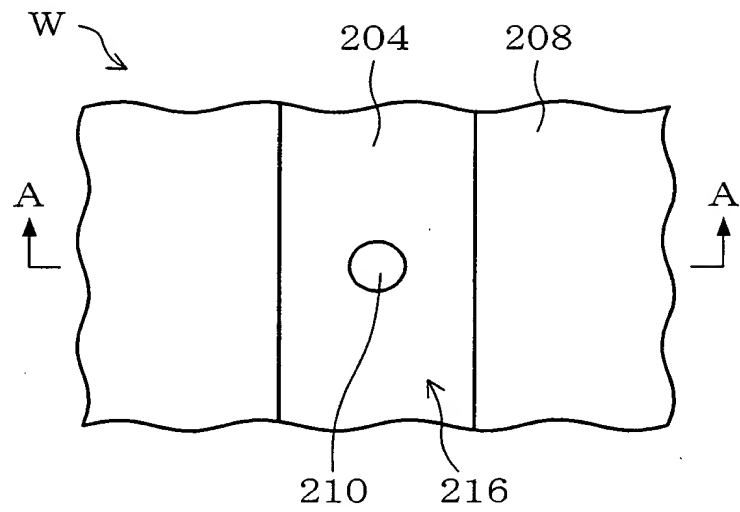


FIG.3(b)

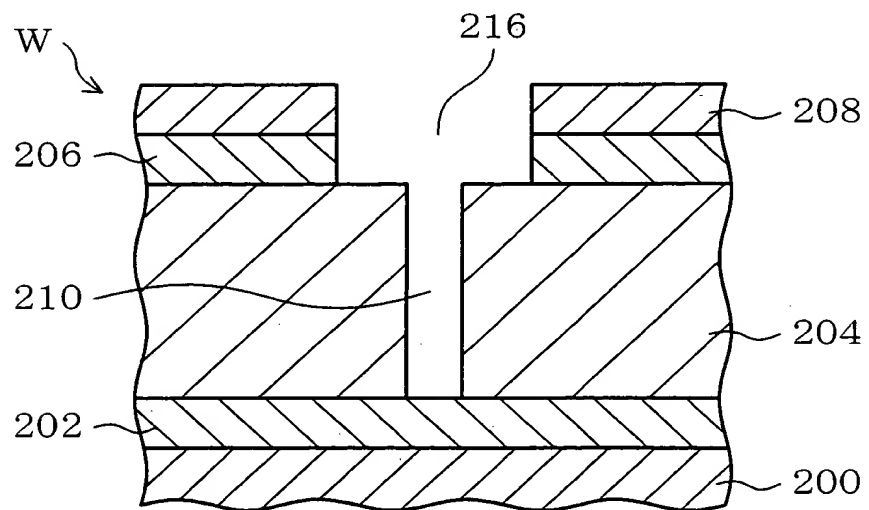


FIG. 4(a)

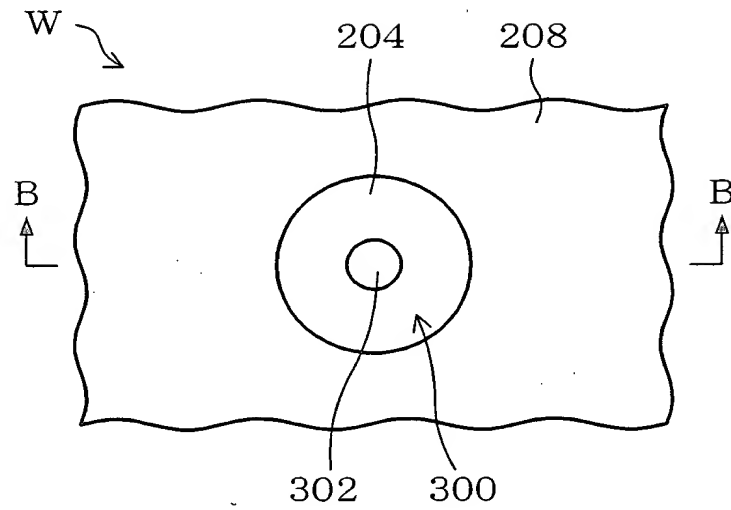


FIG. 4(b)

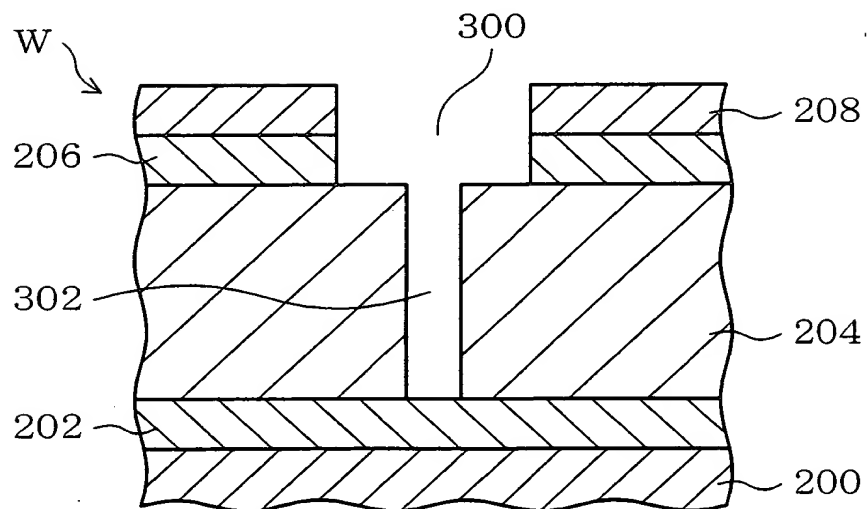


FIG.5(a)

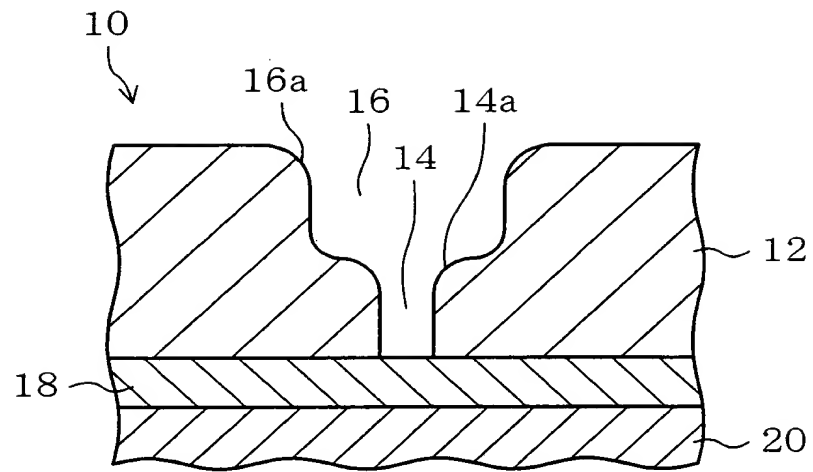


FIG.5(b)

